

L Number	Hits	Search Text	DB	Time stamp
29	3489	136/200-242.ccls.	USPAT	2003/03/04 09:17
30	307	136/200-242.ccls. and via	USPAT	2003/03/04 09:17
31	0		USPAT	2003/03/04 09:34
32	0		USPAT	2003/03/04 09:34
33	1		USPAT	2003/03/04 09:35
34	0	("19 and thermoelectric").PN.	USPAT	2003/03/04 09:35
35	0		USPAT	2003/03/04 09:35
44	2	136/200-242.ccls. and (wafer adj1 bonding)	USPAT	2003/03/04 10:06
45	1	("5598031").PN.	USPAT	2003/03/04 10:14
46	1	("6162659").PN.	USPAT	2003/03/04 10:14
47	1300	wafer adj bonding	USPAT	2003/03/04 10:26
48	0	257/930 and (wafer adj bonding)	USPAT	2003/03/04 10:27
49	131	257/930	USPAT	2003/03/04 10:27
50	0	257/930 and (wafer adj bonding)	USPAT	2003/03/04 10:27
51	9038	257/712 amd (wafer adj bonding)	USPAT	2003/03/04 10:28
52	2021	257/712	USPAT	2003/03/04 10:29
53	6	257/717 and (wafer adj bonding)	USPAT	2003/03/04 10:31
54	6	257/722 and (wafer adj bonding)	USPAT	2003/03/04 10:32
55	2	257/719 and (wafer adj bonding)	USPAT	2003/03/04 10:41
56	6	257/713 and (wafer adj bonding)	USPAT	2003/03/04 10:42
57	44	257/930 and bonding	USPAT	2003/03/04 10:44
58	445	257/\$.ccls. and (wafer adj bonding)	USPAT	2003/03/04 10:55
59	2	(257/\$.ccls. and (wafer adj bonding)) and heatsink	USPAT	2003/03/04 10:45
60	2	136/200-242.ccls. and (wafer adj bonding)	USPAT	2003/03/04 10:48
61	4	(wafer adj bonding) and heatsink	USPAT	2003/03/04 10:49
62	332	136/204	USPAT	2003/03/04 10:58
63	572	136/201	USPAT	2003/03/04 10:59
64	95	136/201 and bonding	USPAT	2003/03/04 11:16
65	443	136/200-242.ccls. and ceramic	USPAT	2003/03/04 11:16
66	156	(136/200-242.ccls. and ceramic) and semiconductor	USPAT	2003/03/04 11:17